

DATA SHEET

BF820W; BF822W NPN high-voltage transistors

Product specification
Supersedes data of 1997 Jun 19
File under Discrete Semiconductors, SC04

1997 Sep 03

NPN high-voltage transistors

BF820W; BF822W

FEATURES

- Low current (max. 50 mA)
- High voltage (max. 300 V).

APPLICATIONS

- Telephony and professional communication equipment.

DESCRIPTION

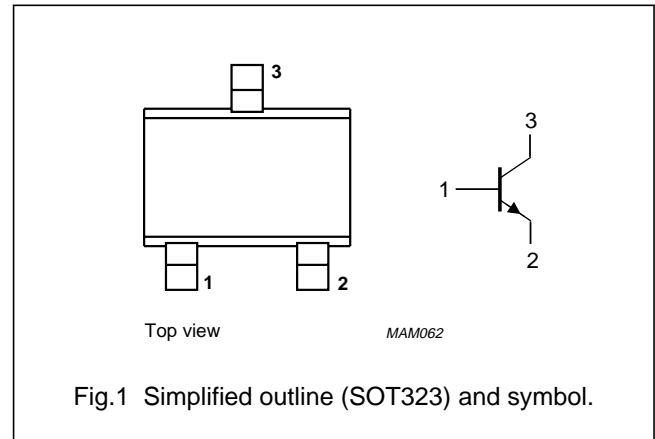
NPN high-voltage transistor in a SOT323 plastic package.

MARKING

TYPE NUMBER	MARKING CODE
BF820W	1Vt
BF822W	1Wt

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BF820W		–	300	V
	BF822W		–	250	V
V _{CEO}	collector-emitter voltage	open base			
	BF820W		–	300	V
	BF822W		–	250	V
I _{CM}	peak collector current		–	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	–	200	mW
h _{FE}	DC current gain	I _C = 25 mA; V _{CE} = 20 V	50	–	
C _{re}	feedback capacitance	I _C = i _c = 0; V _{CB} = 30 V; f = 1 MHz	–	1.6	pF
f _T	transition frequency	I _C = 10 mA; V _{CE} = 10 V; f = 100 MHz	60	–	MHz

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter			
	BF820W		–	300	V
	BF822W		–	250	V
V _{CEO}	collector-emitter voltage	open base			
	BF820W		–	300	V
	BF822W		–	250	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	50	mA
I _{CM}	peak collector current		–	100	mA
I _{BM}	peak base current		–	50	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	200	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 200 V	–	10	nA
		I _E = 0; V _{CB} = 200 V; T _j = 150 °C	–	10	μA
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 5 V	–	50	nA
h _{FE}	DC current gain	I _C = 25 mA; V _{CE} = 20 V	50	–	
V _{CEsat}	collector-emitter saturation voltage	I _C = 30 mA; I _B = 5mA; note 1	–	600	mV
C _{re}	feedback capacitance	I _C = I _c = 0; V _{CB} = 30 V; f = 1 MHz	–	1.6	pF
f _T	transition frequency	I _C = 10 mA; V _{CE} = 10 V; f = 100 MHz	60	–	MHz

Note

1. Pulse test: t_p ≤ 300 μs; δ ≤ 0.02.

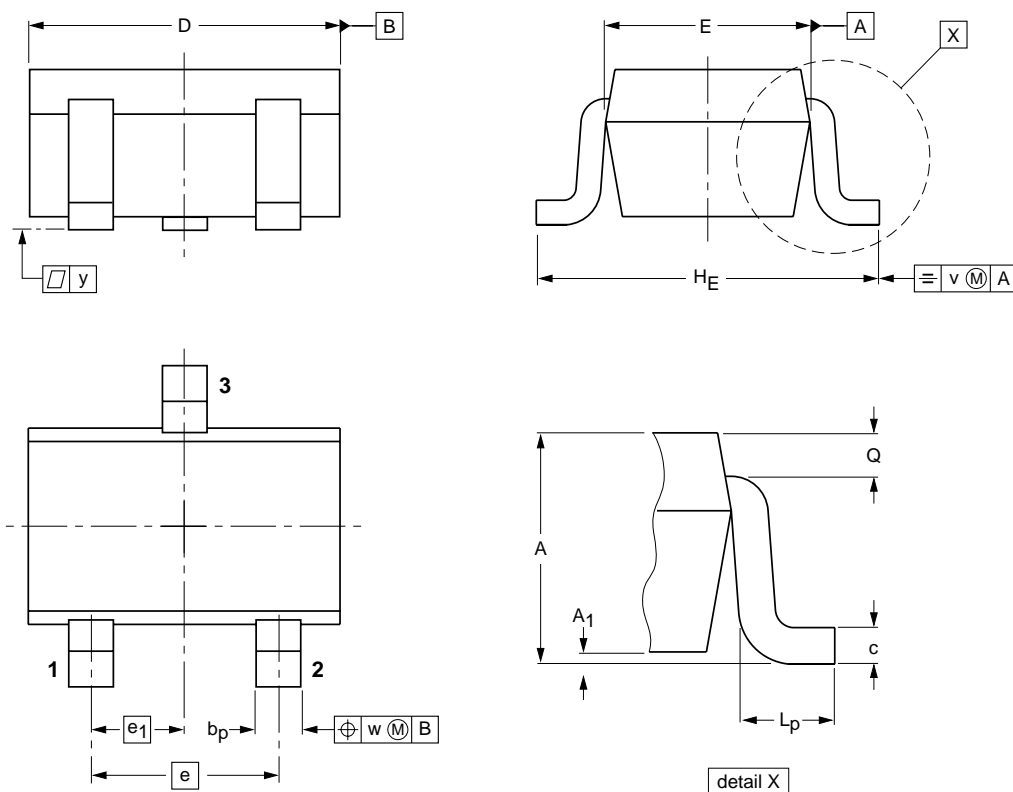
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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NOTES

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